

L10	38	laser same ((compound near semiconductor) sic gan aln bn diamond (aluminum adj nitride) (boron adj nitride) (gallium adj nitride) (silicon adj nitride)) same (bandgap (band adj gap)) same (mocvd "metallo-organic" "organo-metallic" organometallic metal\$1organic)	US-PGPUB; USPAT	OR	ON	2005/02/09 15:52
L11	14	laser and ((compound near semiconductor) sic gan aln bn diamond (aluminum adj nitride) (boron adj nitride) (gallium adj nitride) (silicon adj nitride)) and (bandgap (band adj gap)) and (mocvd "metallo-organic" "organo-metallic" organometallic metal\$1organic)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/09 15:55
L12	48	laser and ((compound near semiconductor) sic gan aln bn diamond (aluminum adj nitride) (boron adj nitride) (gallium adj nitride) (silicon adj nitride)) and (diode transistor fet bjt bipolar m?sfet) and (mocvd "metallo-organic" "organo-metallic" organometallic metal\$1organic)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/09 16:25
L13	349	(438/237.ccls. 438/328.ccls. 438/335.ccls. 438/378.ccls. 438/380.ccls. 438/535.ccls. 438/667.ccls. 438/681.ccls.) and laser	US-PGPUB; USPAT	OR	ON	2005/02/09 16:33
L14	195	laser same ((compound near semiconductor) sic gan aln bn diamond (aluminum adj nitride) (boron adj nitride) (gallium adj nitride) (silicon adj nitride)) same (diode transistor fet bjt bipolar m?sfet) same (mocvd "metallo-organic" "organo-metallic" organometallic metal\$1organic)	US-PGPUB; USPAT	OR	ON	2005/02/09 16:42

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	"6670693".URPN.	USPAT	OR	OFF	2005/02/09 15:11
L2	2	"6271576".URPN.	USPAT	OR	OFF	2005/02/09 15:11
L3	4	"5837607".URPN.	USPAT	OR	OFF	2005/02/09 15:13
L4	4	"6025609".URPN.	USPAT	OR	OFF	2005/02/09 15:17
L5	3	"6054375".URPN.	USPAT	OR	OFF	2005/02/09 15:19
L6	5	(438/237.ccls. 438/328.ccls. 438/335.ccls. 438/378.ccls. 438/380.ccls. 438/535.ccls. 438/667.ccls. 438/681.ccls.) and (laser near2 synthesi\$6)	US-PGPUB; USPAT	OR	ON	2005/02/09 15:20
L7	10	(laser near2 synthesi\$6) and ((compound near semiconductor) sic gan aln bn diamond (aluminum adj nitride) (boron adj nitride) (gallium adj nitride) (silicon adj nitride) mocvd "metallo-organic" "organo-metallic" organometallic metal\$1organic bandgap (band adj gap))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/09 15:29
L8	255	(laser near2 synthesi\$6) and ((compound near semiconductor) sic gan aln bn diamond (aluminum adj nitride) (boron adj nitride) (gallium adj nitride) (silicon adj nitride) mocvd "metallo-organic" "organo-metallic" organometallic metal\$1organic bandgap (band adj gap))	US-PGPUB; USPAT	OR	ON	2005/02/09 15:30
L9	5	(438/237.ccls. 438/328.ccls. 438/335.ccls. 438/378.ccls. 438/380.ccls. 438/535.ccls. 438/667.ccls. 438/681.ccls.) and (laser same ((compound near semiconductor) sic gan aln bn diamond (aluminum adj nitride) (boron adj nitride) (gallium adj nitride) (silicon adj nitride) bandgap (band adj gap)) same (mocvd "metallo-organic" "organo-metallic" organometallic metal\$1organic))	US-PGPUB; USPAT	OR	ON	2005/02/09 15:48